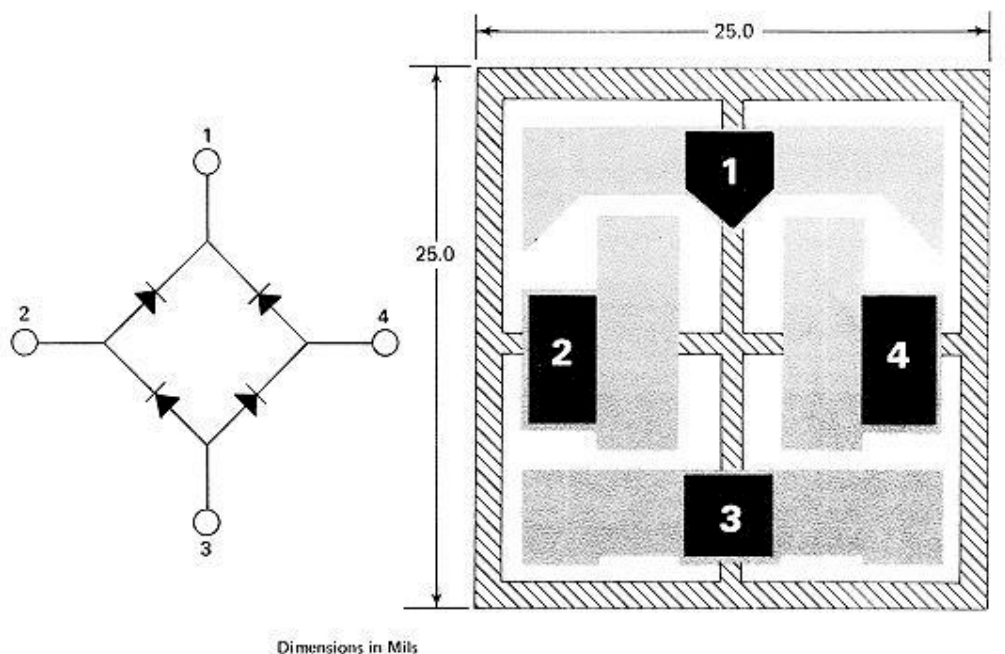


DIONICS INC.

65 RUSHMORE ST., WESTBURY, N.Y. 11590
516 • 997 • 7474 TWX 510 • 222 • 0974



DI 914 B Dielectrically Isolated DIODE QUAD BRIDGE



Dielectric Isolation Aluminum Bonding Area

- Chip Thickness=6 Mils \pm 1 Mil
- Min. Dimension Across Bonding Pads=4.0 Mils
- Min. Separation Between Bonding Pads=1.75 Mils
- Distance from Bonding Pads to Edge of Chips=1.75 Mils

PRINTED IN USA
11-75

Detailed Specifications on Reverse Side

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DI 914 B Dielectrically Isolated DIODE QUAD BRIDGE

- Dielectric Isolation • Monolithic Construction • Superior Thermal Tracking
- Close Parameter Match • Available in Chip Form

For use in hybrid circuits.

Among the features are: Dielectric Isolation; monolithic construction; close parameter match; and superior thermal tracking. The use of this versatile chip provides a savings in space, as well as reduced die-bonding time at harmful elevated temperatures. Aluminum metallizing on bonding pads permits utilization of conventional wire-bonding techniques.

The 4 diodes are Dielectrically Isolated from each other and from the bottom of the chip, with more than 1,000 volts isolation between individual

diodes.

The chips are gold-backed, permitting conventional eutectic die-bonding techniques.

Since the bottom of the DI chip is not used for electrical contact, it is possible to die-bond with pure epoxy or adhesive films. Excellent mechanical and thermal properties are thus easily achieved, without the substrate or its components being subjected to high temperatures. Chips are shipped in 2" x 2" plastic compartmented containers, 400 chips in each container, with each chip in its own compartment.

← 100% Probe Tested to These Parameters @ 25°C →
(tested on sample basis)

	V_{BR} (Each Diode) Volts Min. @ $I_R = 100 \mu A$	I_R (Each Diode) μA Max. @ V_R Volts	I_F (Each Diode) mA Min. @ $V_F = 1.0V$	C_T (Each Diode) pf Max.	t_{rr} Max. (Each Diode) @ $I_F = 10mA$; recover to $I_{RR} = 1 mA$
DI 914-B	75	.010 @ 65			
-.2B	60	.010 @ 50	20	3.0	*500 nsec.
-.3B	45	.010 @ 35			

*Also available in gold doped version with T_{rr} as low as 3.0nsec.

Dimensional Drawing on Reverse Side